

**SINGLE BUFFER/DRIVER WITH OPEN DRAIN OUTPUT**
**Description**

The Advanced Ultra Low Power (AUP) CMOS logic family is designed for low power and extended battery life in portable applications.

The 74AUP1G07 is a single buffer gate with an open drain output designed for operation over a power supply range of 0.8V to 3.6V.

The device is fully specified for partial power down applications using I<sub>OFF</sub>. The I<sub>OFF</sub> circuitry disables the output preventing damaging current backflow when the device is powered down. The gate performs the positive Boolean function:

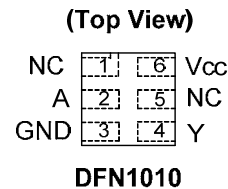
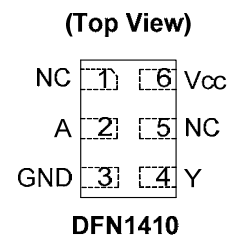
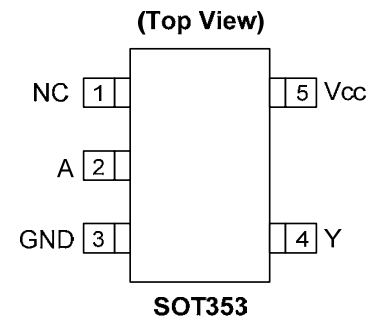
$$Y = A$$

**Features**

- Advanced Ultra Low Power (AUP) CMOS
- Supply Voltage Range from 0.8V to 3.6V
- 4 mA Output Drive at 3.0V
- Low Static power consumption
  - I<sub>CC</sub> < 0.9µA
- Low Dynamic Power Consumption
  - C<sub>PD</sub> = 6pF (Typical at 3.6V)
- Schmitt Trigger Action at All Inputs Make the Circuit Tolerant for Slower Input Rise and Fall Time. The hysteresis is typically 250 mV at V<sub>CC</sub> = 3.0V
- I<sub>OFF</sub> Supports Partial-Power-Down Mode Operation
- ESD Protection Exceeds JESD 22
  - 2000-V Human Body Model (A114-A)
  - Exceeds 1000-V Charged Device Model (C101C)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options SOT353, DFN1410, and DFN1010
- Leadless packages per JESD30E
  - DFN1010 denoted as X2-DFN1010-6
  - DFN1014 denoted as X2-DFN1014-6
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.  
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.  
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

[Click here for ordering information, located at the end of datasheet](#)

**Pin Assignments**

**Applications**

- Suited for battery and low power needs
- Wide array of products such as:
- Tablets, E-readers
  - Cell Phones, Personal Navigation / GPS
  - MP3 players, Cameras, Video Recorders
  - PCs ultrabooks, notebooks, netbooks,
  - Computer peripherals, hard drives, CD/DVD ROM
  - TV, DVD, DVR, set top box

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**Pin Descriptions**

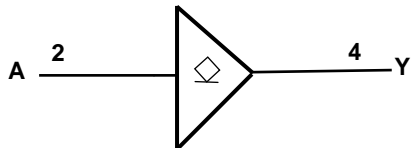
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Pin Name	Function
NC	No Connection
A	Data Input
GND	Ground
Y	Data Output
V <sub>CC</sub>	Supply Voltage

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**Logic Diagram**

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**Function Table**

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Inputs	Output
A	Y
H	Z
L	L

### Absolute Maximum Ratings (Note 4) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Parameter	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD CDM	Charged Device Model ESD Protection	1	KV
V <sub>CC</sub>	Supply Voltage Range	-0.5 to +4.6	V
V <sub>I</sub>	Input Voltage Range	-0.5 to +4.6	V
V <sub>O</sub>	Voltage applied to output in high or low state	-0.5 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> < 0	50	mA
I <sub>OK</sub>	Output Clamp Current (V <sub>O</sub> < 0)	50	mA
I <sub>O</sub>	Continuous output current (V <sub>O</sub> = 0 to V <sub>CC</sub> )	±20	mA
I <sub>CC</sub>	Continuous current through V <sub>CC</sub>	50	mA
I <sub>GND</sub>	Continuous current through GND	-50	mA
T <sub>J</sub>	Operating Junction Temperature	-40 to +150	°C
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C

Note: 4. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

### Recommended Operating Conditions (Note 5) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Parameter	Min	Max	Unit
V <sub>CC</sub>	Operating Voltage	0.8	3.6	V
V <sub>I</sub>	Input Voltage	0	3.6	V
V <sub>O</sub>	Output Voltage	0	V <sub>CC</sub>	V
I <sub>OL</sub>	Low-Level Output Current	V <sub>CC</sub> = 0.8V	20	mA
		V <sub>CC</sub> = 1.1V	1.1	
		V <sub>CC</sub> = 1.4V	1.7	
		V <sub>CC</sub> = 1.65V	1.9	
		V <sub>CC</sub> = 2.3V	3.1	
		V <sub>CC</sub> = 3.0V	4	
Δt/ΔV	Input Transition Rise or Fall Rate		200	ns/V
T <sub>A</sub>	Operating Free-Air Temperature	-40	+125	°C

Note: 5. Unused inputs should be held at V<sub>CC</sub> or Ground.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	V <sub>CC</sub>	T <sub>A</sub> = +25°C		T <sub>A</sub> = -40°C to +85°C		Unit
				Min	Max	Min	Max	
V <sub>IH</sub>	High-Level Input Voltage		0.8V to 1.65V	0.80 X V <sub>CC</sub>		0.80 X V <sub>CC</sub>		V
			1.65V to 1.95V	0.65 X V <sub>CC</sub>		0.65 X V <sub>CC</sub>		
			2.3V to 2.7V	1.6		1.6		
			3.0V to 3.6V	2.0		2.0		
V <sub>IL</sub>	Low-Level Input Voltage		0.8V to 1.65V		0.30 X V <sub>CC</sub>		0.30 X V <sub>CC</sub>	V
			1.65V to 1.95V		0.35 X V <sub>CC</sub>		0.35 X V <sub>CC</sub>	
			2.3V to 2.7V		0.7		0.7	
			3.0V to 3.6V		0.9		0.9	
V <sub>OL</sub>	High-Level Input Voltage	I <sub>OL</sub> = 20μA	0.8V to 3.6V		0.1		0.1	V
		I <sub>OL</sub> = 1.1mA	1.1V		0.3 X V <sub>CC</sub>		0.3 X V <sub>CC</sub>	
		I <sub>OL</sub> = 1.7mA	1.4V		0.31		0.37	
		I <sub>OL</sub> = 1.9mA	1.65V		0.31		0.35	
		I <sub>OL</sub> = 2.3mA	2.3V		0.31		0.33	
		I <sub>OL</sub> = 3.1mA			0.44		0.45	
		I <sub>OL</sub> = 2.7mA	3V		0.31		0.33	
		I <sub>OL</sub> = 4mA			0.44		0.45	
I <sub>I</sub>	Input Current	A or B Input V <sub>I</sub> = GND to 3.6V	0V to 3.6V		± 0.1		± 0.5	μA
I <sub>OFF</sub>	Power Down Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 0V to 3.6V	0		± 0.2		± 0.5	μA
I <sub>OZ</sub>	Z State Leakage Current	V <sub>O</sub> = 3.6V V <sub>I</sub> = 3.6V	3.6V		± 0.2		± 0.5	μA
ΔI <sub>OFF</sub>	Delta Power Down Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 0V to 3.6V	0V to 0.2 V		0.2		0.6	μA
I <sub>CC</sub>	Supply Current	V <sub>I</sub> = GND or V <sub>CC</sub> , I <sub>O</sub> =0	0.8V to 3.6V		0.5		0.9	μA
ΔI <sub>CC</sub>	Additional Supply Current	Input at V <sub>CC</sub> -0.6V	3.3V		40		50	μA

**Electrical Characteristics** (cont.) (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Symbol	Parameter	Test Conditions	V <sub>CC</sub>	T <sub>A</sub> = -40°C to +125°C		Unit
				Min	Max	
V <sub>IH</sub>	High-Level Input Voltage		0.8V to 1.65V	0.80 X V <sub>CC</sub>		V
			1.65V to 1.95V	0.70 X V <sub>CC</sub>		
			2.3V to 2.7V	1.6		
			3.0V to 3.6V	2.0		
V <sub>IL</sub>	Low-Level Input Voltage		0.8V to 1.65V		0.25X V <sub>CC</sub>	V
			1.65V to 1.95V		0.35 X V <sub>CC</sub>	
			2.3V to 2.7V		0.7	
			3.0V to 3.6V		0.9	
V <sub>OL</sub>	High-Level Input Voltage	I <sub>OL</sub> = 20μA	0.8V to 3.6V		0.11	V
		I <sub>OL</sub> = 1.1mA	1.1V		0.3 X V <sub>CC</sub>	
		I <sub>OL</sub> = 1.7mA	1.4V		0.41	
		I <sub>OL</sub> = 1.9mA	1.65V		0.39	
		I <sub>OL</sub> = 2.3mA	2.3V		0.36	
		I <sub>OL</sub> = 3.1mA			0.50	
		I <sub>OL</sub> = 2.7mA	3V		0.36	
		I <sub>OL</sub> = 4mA			0.50	
I <sub>I</sub>	Input Current	A or B Input V <sub>I</sub> = GND to 3.6V	0V to 3.6V		± 0.75	μA
I <sub>OFF</sub>	Power Down Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 0V to 3.6V	0		± 3.5	μA
I <sub>OZ</sub>	Z State Leakage Current	V <sub>O</sub> = 3.6V V <sub>I</sub> = 3.6V	3.6V		± 1.5	μA
ΔI <sub>OFF</sub>	Delta Power Down Leakage Current	V <sub>I</sub> or V <sub>O</sub> = 0V to 3.6V	0V to 0.2V		± 2.5	μA
I <sub>CC</sub>	Supply Current	V <sub>I</sub> = GND or V <sub>CC</sub> , I <sub>O</sub> = 0	0.8V to 3.6V		3.0	μA
ΔI <sub>CC</sub>	Additional Supply Current	Input at V <sub>CC</sub> -0.6V	3.3V		75	μA

## Switching Characteristics

 $C_L = 5\text{pF}$  see Figure 1

Parameter	From Input	TO OUTPUT	V <sub>CC</sub>	T <sub>A</sub> = +25°C			T <sub>A</sub> = -40°C to +85°C		T <sub>A</sub> = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t <sub>pd</sub>	A	Y	0.8V		11.6						ns
			1.2V ± 0.1V	2.0	4.1	7.5	2.0	9.1	2.0	10.0	
			1.5V ± 0.1V	1.5	3.0	5.1	1.5	6.1	1.5	6.7	
			1.8V ± 0.15V	1.2	2.7	4.0	1.2	5.0	1.2	5.5	
			2.5V ± 0.2V	1.0	2.3	3.2	1.0	4.0	1.0	4.4	
			3.3V ± 0.3V	0.8	2.2	2.8	0.8	3.3	0.8	3.6	

 $C_L = 10\text{pF}$  see Figure 1

Parameter	From Input	TO OUTPUT	V <sub>CC</sub>	T <sub>A</sub> = +25°C			T <sub>A</sub> = -40°C to +85°C		T <sub>A</sub> = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t <sub>pd</sub>	A	Y	0.8V		14.7						ns
			1.2V ± 0.1V	2.5	5.1	9.0	2.5	11.2	2.5	12.3	
			1.5V ± 0.1V	2.0	3.8	6.1	2.0	7.4	2.0	8.1	
			1.8V ± 0.15V	1.7	3.6	4.8	1.7	6.1	1.7	6.7	
			2.5V ± 0.2V	1.4	3.3	4.5	1.4	4.8	1.4	5.3	
			3.3V ± 0.3V	1.2	3.1	4.2	1.2	4.5	1.2	5.0	

 $C_L = 15\text{pF}$  see Figure 1

Parameter	From Input	TO OUTPUT	V <sub>CC</sub>	T <sub>A</sub> = +25°C			T <sub>A</sub> = -40°C to +85°C		T <sub>A</sub> = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t <sub>pd</sub>	A	Y	0.8V		17.7						ns
			1.2V ± 0.1V	2.9	6.1	10.4	2.9	13.1	2.9	14.5	
			1.5V ± 0.1V	2.3	4.5	6.8	2.3	8.6	2.3	9.4	
			1.8V ± 0.15V	2.1	4.4	6.7	2.1	7.8	2.1	8.6	
			2.5V ± 0.2V	1.7	4.2	5.9	1.7	6.8	1.7	6.9	
			3.3V ± 0.3V	1.5	4.0	5.7	1.5	6.1	1.5	6.7	

 $C_L = 30\text{pF}$  see Figure 1

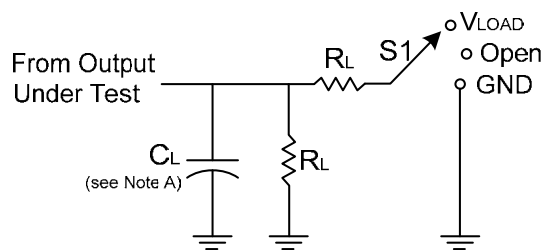
Parameter	From Input	TO OUTPUT	V <sub>CC</sub>	T <sub>A</sub> = +25°C			T <sub>A</sub> = -40°C to +85°C		T <sub>A</sub> = -40°C to +125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t <sub>pd</sub>	A	Y	0.8V		24.6						ns
			1.2V ± 0.1V	3.9	9.0	15.6	3.9	18.8	3.9	20.7	
			1.5V ± 0.1V	3.2	7.5	13.4	3.2	13.7	3.2	13.7	
			1.8V ± 0.15V	2.9	6.8	12.4	2.9	12.6	2.9	12.6	
			2.5V ± 0.2V	2.5	6.5	10.7	2.5	10.9	2.5	12.1	
			3.3V ± 0.3V	2.3	6.4	9.7	2.3	10.4	2.3	11.4	

**Operating and Package Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Parameter		Test Conditions		V <sub>CC</sub>	Typ	Unit
C <sub>pd</sub>	Power Dissipation Capacitance	f = 1MHz	No Load	0.8V	2.6	pF
				1.2V ± 0.1V	2.8	
				1.5V ± 0.1V	2.9	
				1.8V ± 0.15V	3.1	
				2.5V ± 0.2V	3.6	
				3.3V ± 0.3V	4.2	
C <sub>i</sub>	Input Capacitance	V <sub>i</sub> = V <sub>CC</sub> or GND		0V or 3.3V	1.5	pF
θ <sub>JA</sub>	Thermal Resistance Junction-to-Ambient	SOT353	(Note 6)		371	°C/W
		X2-DFN1410-6		430		
		X2-DFN1010-6		445		
θ <sub>JC</sub>	Thermal Resistance Junction-to-Case	SOT353	(Note 6)		143	°C/W
		X2-DFN1410-6		190		
		X2-DFN1010-6		250		

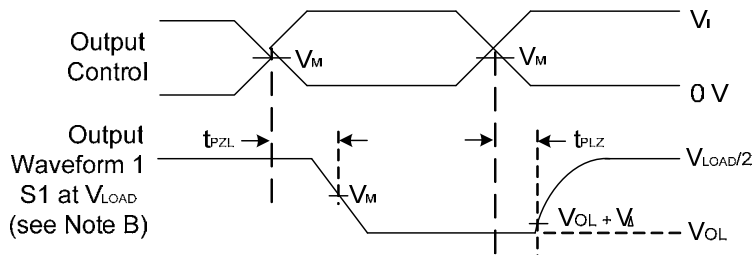
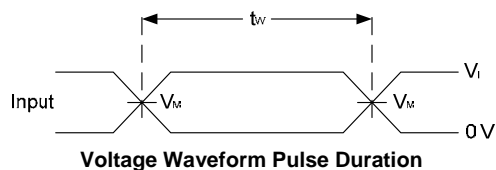
Notes: 6. Test condition for SOT353, X2-DFN1410-6, and X2-DFN1010-6 devices mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

**Parameter Measurement Information**



TEST	S1	R <sub>L</sub>
t <sub>PLZ</sub> /t <sub>PZL</sub>	V <sub>LOAD</sub>	5KΩ

V <sub>CC</sub>	Inputs		V <sub>M</sub>	V <sub>LOAD</sub>	C <sub>L</sub>	V <sub>Δ</sub>
	V <sub>I</sub>	t <sub>r</sub> /t <sub>f</sub>				
0.8V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.1V
1.2V±0.1V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.1V
1.5V±0.1V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.1V
1.8V±0.15V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.15V
2.5V±0.2V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.15V
3.3V±0.3 V	V <sub>CC</sub>	≤3ns	V <sub>CC</sub> /2	2 X V <sub>CC</sub>	5, 10, 15, 30pF	0.3V

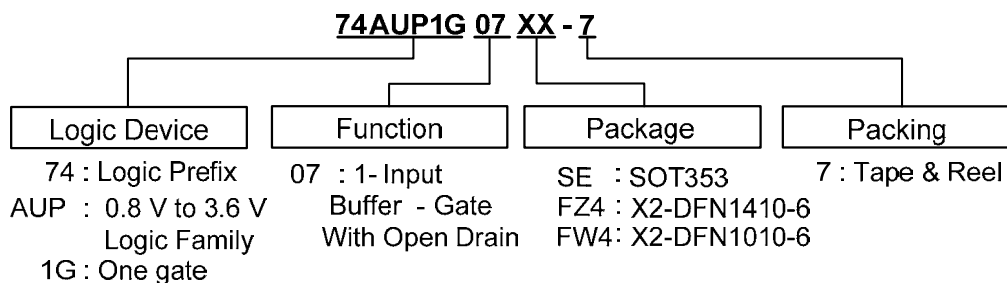


**Voltage Waveform Enable and Disable Times Low and High Level Enabling**

**Figure 1. Load Circuit and Voltage Waveforms**

- Notes: A. Includes test lead and test apparatus capacitance.  
 B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.  
 C. Inputs are measured separately one transition per measurement.  
 D. For the open drain device the specified propagation delay t<sub>PD</sub> is the same as t<sub>PLZ</sub> and t<sub>PZL</sub>.

## Ordering Information

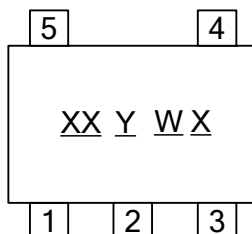


Part Number	Package Code	Packaging	7" Tape and Reel	
			Quantity	Part Number Suffix
74AUP1G07SE-7	SE	SOT353	3000/Tape & Reel	-7
74AUP1G07FZ4-7	FZ4	X2-DFN1410-6	5000/Tape & Reel	-7
74AUP1G07FW4-7	FW4	X2-DFN1010-6	5000/Tape & Reel	-7

## Marking Information

### (1) SOT353

(Top View)

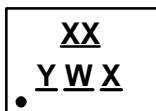


**XX** : Identification code  
**Y** : Year 0~9  
**W** : Week : A~Z : 1~26 week;  
           a~z : 27~52 week; z represents  
           52 and 53 week  
**X** : A~Z : Internal code

Part Number	Package	Identification Code
74AUP1G07SE	SOT353	XN

### (2) X2-DFN1410-6 and X2-DFN1010-6

(Top View)



**XX** : Identification Code  
**Y** : Year : 0~9  
**W** : Week : A~Z : 1~26 week;  
           a~z : 27~52 week; z represents  
           52 and 53 week  
**X** : A~Z : Internal code

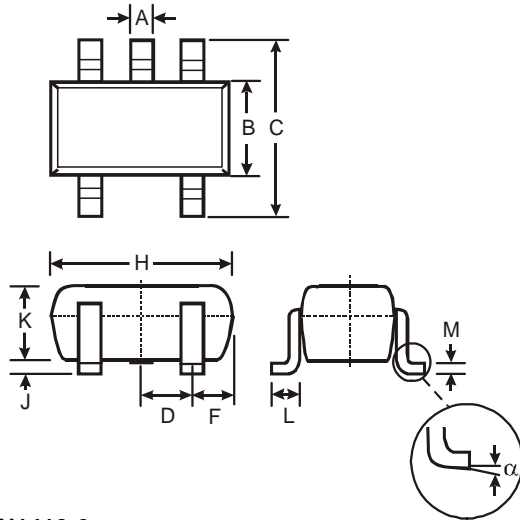
Part Number	Package	Identification Code
74AUP1G07FZ4	X2-DFN1410-6	XN
74AUP1G07FW4	X2-DFN1010-6	XN



**Package Outline Dimensions** (All dimensions in mm.)

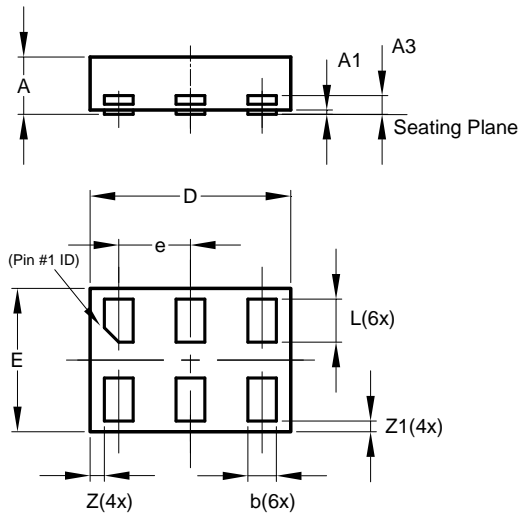
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.

(1) SOT353



SOT353			
Dim	Min	Max	Typ
A	0.10	0.30	0.25
B	1.15	1.35	1.30
C	2.00	2.20	2.10
D	0.65 Typ		
F	0.40	0.45	0.425
H	1.80	2.20	2.15
J	0	0.10	0.05
K	0.90	1.00	1.00
L	0.25	0.40	0.30
M	0.10	0.22	0.11
α	0°	8°	-
All Dimensions in mm			

(2) X2-DFN1410-6

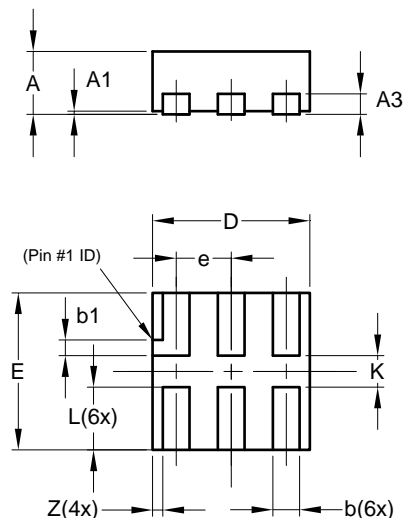


X2-DFN1410-6			
Dim	Min	Max	Typ
A	—	0.40	0.39
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.15	0.25	0.20
D	1.35	1.45	1.40
E	0.95	1.05	1.00
e	—	—	0.50
L	0.25	0.35	0.30
Z	—	—	0.10
Z1	0.045	0.105	0.075
All Dimensions in mm			

**Package Outline Dimensions** (cont.) (All dimensions in mm.)

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for latest version.

**(3) X2-DFN1010-6**

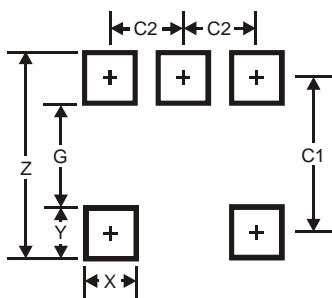


X2-DFN1010-6			
Dim	Min	Max	Typ
A	—	0.40	0.39
A1	0.00	0.05	0.02
A3	—	—	0.13
b	0.14	0.20	0.17
b1	0.05	0.15	0.10
D	0.95	1.05	1.00
E	0.95	1.05	1.00
e	—	—	0.35
L	0.35	0.45	0.40
K	0.15	—	—
Z	—	—	0.065
All Dimensions in mm			

**Suggested Pad Layout**

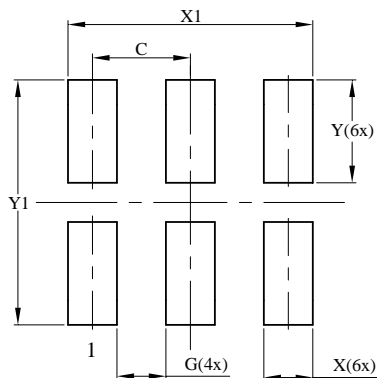
Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version

**(1) SOT353**



Dimensions	Value (in mm)
Z	2.5
G	1.3
X	0.42
Y	0.6
C1	1.9
C2	0.65

**(2) X2-DFN1410-6**

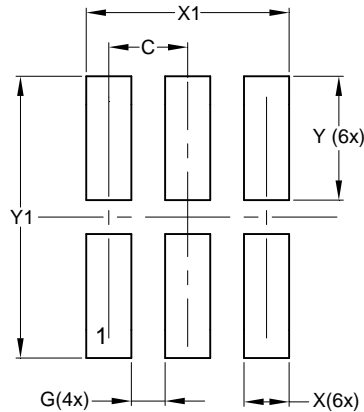


Dimensions	Value (in mm)
C	0.500
G	0.250
X	0.250
X1	1.250
Y	0.525
Y1	1.250

**Suggested Pad Layout** (cont.)

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

**(3) X2-DFN1010-6**



Dimensions	Value (in mm)
C	0.350
G	0.150
X	0.200
X1	0.900
Y	0.550
Y1	1.250

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